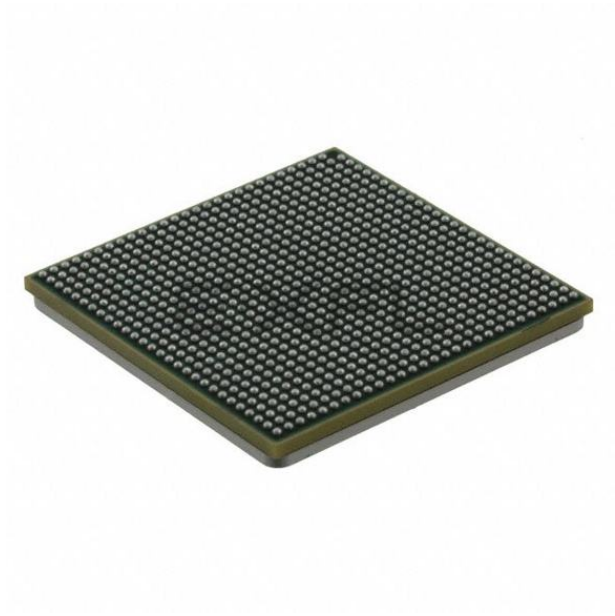

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.2GHz
Co-Processors/DSP	Signal Processing; SPE, Security; SEC
RAM Controllers	DDR, DDR2, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8548ecvtatgb

— Performance monitor facility that is similar to, but separate from, the device performance monitor

The e500 defines features that are not implemented on this device. It also generally defines some features that this device implements more specifically. An understanding of these differences can be critical to ensure proper operations.

- 512-Kbyte L2 cache/SRAM
  - — Flexible configuration.
  - — Full ECC support on 64-bit boundary in both cache and SRAM modes
  - — Cache mode supports instruction caching, data caching, or both.
  - — External masters can force data to be allocated into the cache through programmed memory ranges or special transaction types (stashing).
  - — 1, 2, or 4 ways can be configured for stashing only.
  - — Eight-way set-associative cache organization (32-byte cache lines)
  - — Supports locking entire cache or selected lines. Individual line locks are set and cleared through Book E instructions or by externally mastered transactions.
  - — Global locking and Flash clearing done through writes to L2 configuration registers
  - — Instruction and data locks can be Flash cleared separately.
  - — SRAM features include the following:
    - – I/O devices access SRAM regions by marking transactions as snoopable (global).
    - – Regions can reside at any aligned location in the memory map.
    - – Byte-accessible ECC is protected using read-modify-write transaction accesses for smaller-than-cache-line accesses.
- Address translation and mapping unit (ATMU)
  - — Eight local access windows define mapping within local 36-bit address space.
  - — Inbound and outbound ATMUs map to larger external address spaces.
    - – Three inbound windows plus a configuration window on PCI/PCI-X and PCI Express
    - – Four inbound windows plus a default window on RapidIO™
    - – Four outbound windows plus default translation for PCI/PCI-X and PCI Express
    - – Eight outbound windows plus default translation for RapidIO with segmentation and sub-segmentation support
- DDR/DDR2 memory controller
  - — Programmable timing supporting DDR and DDR2 SDRAM
  - — 64-bit data interface
  - — Four banks of memory supported, each up to 4 Gbytes, to a maximum of 16 Gbytes
  - — DRAM chip configurations from 64 Mbits to 4 Gbits with ×8/×16 data ports
  - — Full ECC support
  - — Page mode support
    - – Up to 16 simultaneous open pages for DDR

  - VRRP and HSRP support for seamless router fail-over
  - Up to 16 exact-match MAC addresses supported
  - Broadcast address (accept/reject)
  - Hash table match on up to 512 multicast addresses
  - Promiscuous mode
- Buffer descriptors backward compatible with MPC8260 and MPC860T 10/100 Ethernet programming models
- RMON statistics support
- 10-Kbyte internal transmit and 2-Kbyte receive FIFOs
- MII management interface for control and status
- Ability to force allocation of header information and buffer descriptors into L2 cache

- OCeaN switch fabric
  - Full crossbar packet switch
  - Reorders packets from a source based on priorities
  - Reorders packets to bypass blocked packets
  - Implements starvation avoidance algorithms
  - Supports packets with payloads of up to 256 bytes
- Integrated DMA controller
  - Four-channel controller
  - All channels accessible by both the local and remote masters
  - Extended DMA functions (advanced chaining and striding capability)
  - Support for scatter and gather transfers
  - Misaligned transfer capability
  - Interrupt on completed segment, link, list, and error
  - Supports transfers to or from any local memory or I/O port
  - Selectable hardware-enforced coherency (snoop/no snoop)
  - Ability to start and flow control each DMA channel from external 3-pin interface
  - Ability to launch DMA from single write transaction
- Two PCI/PCI-X controllers
  - PCI 2.2 and PCI-X 1.0 compatible
  - One 32-/64-bit PCI/PCI-X port with support for speeds of up to 133 MHz (maximum PCI-X frequency in synchronous mode is 110 MHz)
  - One 32-bit PCI port with support for speeds from 16 to 66 MHz (available when the other port is in 32-bit mode)
  - Host and agent mode support
  - 64-bit dual address cycle (DAC) support
  - PCI-X supports multiple split transactions
  - Supports PCI-to-memory and memory-to-PCI streaming

6 DDR and DDR2 SDRAM

This section describes the DC and AC electrical specifications for the DDR SDRAM interface of the device. Note that GV_{DD}(typ) = 2.5 V for DDR SDRAM, and GV_{DD}(typ) = 1.8 V for DDR2 SDRAM.

6.1 DDR SDRAM DC Electrical Characteristics

The following table provides the recommended operating conditions for the DDR2 SDRAM controller of the device when GV_{DD}(typ) = 1.8 V.

Table 11. DDR2 SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	1.71	1.89	V	1
I/O reference voltage	MV_{REF}	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	V_{TT}	$MV_{REF} - 0.04$	$MV_{REF} + 0.04$	V	3
Input high voltage	V_{IH}	$MV_{REF} + 0.125$	$GV_{DD} + 0.3$	V	—
Input low voltage	V_{IL}	–0.3	$MV_{REF} - 0.125$	V	—
Output leakage current	I_{OZ}	–50	50	μA	4
Output high current (V_{OUT} = 1.420 V)	I_{OH}	–13.4	—	mA	—
Output low current (V_{OUT} = 0.280 V)	I_{OL}	13.4	—	mA	—

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM V_{DD} at all times.
2. MV_{REF} is expected to be equal to $0.5 \times GV_{DD}$, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail must track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, $0 V \le V_{OUT} \le GV_{DD}$.

This table provides the DDR2 I/O capacitance when GV_{DD}(typ) = 1.8 V.

Table 12. DDR2 SDRAM Capacitance for GV_{DD}(typ)=1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. GV_{DD} = 1.8 V ± 0.090 V, f = 1 MHz, T_A = 25°C, $V_{OUT} = GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.2 V.

Figure 4 shows the DDR SDRAM output timing diagram.+

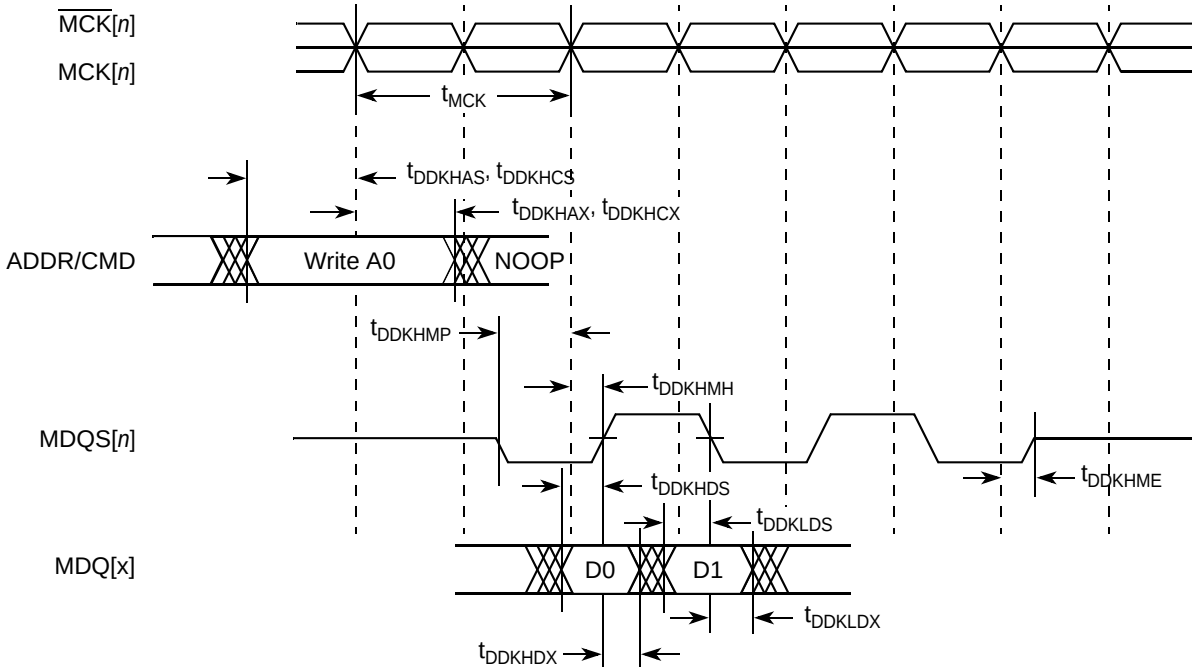

Figure 4. DDR SDRAM Output Timing Diagram

Figure 5 provides the AC test load for the DDR bus.

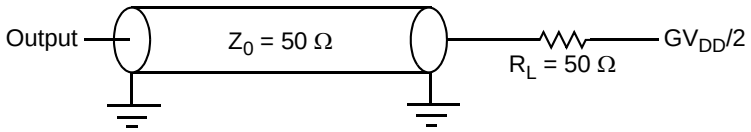

Figure 5. DDR AC Test Load

7 DUART

This section describes the DC and AC electrical specifications for the DUART interface of the device.

7.1 DUART DC Electrical Characteristics

This table provides the DC electrical characteristics for the DUART interface.

Table 20. DUART DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current (V_{IN}[1] = 0 V or V_{IN} = V_{DD})	I_{IN}	—	±5	μA
High-level output voltage (OV_{DD} = min, I_{OH} = –2 mA)	V_{OH}	2.4	—	V
Low-level output voltage (OV_{DD} = min, I_{OL} = 2 mA)	V_{OL}	—	0.4	V

Note:
1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

7.2 DUART AC Electrical Specifications

This table provides the AC timing parameters for the DUART interface.

Table 21. DUART AC Timing Specifications

Parameter	Value	Unit	Notes
Minimum baud rate	f_{CCB}/1,048,576	baud	1, 2
Maximum baud rate	f_{CCB}/16	baud	1, 2, 3
Oversample rate	16	—	1, 4

Notes:
1. Guaranteed by design.
2. f_{CCB} refers to the internal platform clock.
3. Actual attainable baud rate is limited by the latency of interrupt processing.
4. The middle of a start bit is detected as the 8^{th} sampled 0 after the 1-to-0 transition of the start bit. Subsequent bit values are sampled each 16^{th} sample.

8 Enhanced Three-Speed Ethernet (eTSEC)

This section provides the AC and DC electrical characteristics for the enhanced three-speed Ethernet controller. The electrical characteristics for MDIO and MDC are specified in Section 9, "Ethernet Management Interface Electrical Characteristics."

8.1 Enhanced Three-Speed Ethernet Controller (eTSEC) (10/100/1Gb Mbps)—GMII/MII/TBI/RGMII/RTBI/RMII Electrical Characteristics

The electrical characteristics specified here apply to all gigabit media independent interface (GMII), media independent interface (MII), ten-bit interface (TBI), reduced gigabit media independent interface (RGMII), reduced ten-bit interface (RTBI), and reduced media independent interface (RMII) signals except management data input/output (MDIO) and management data clock (MDC). The RGMII and RTBI interfaces are defined for 2.5 V, while the GMII, MII, and TBI interfaces can be operated at 3.3 or 2.5 V. The GMII, MII, or TBI interface timing is compliant with the IEEE 802.3. The RGMII and RTBI interfaces follow the *Reduced Gigabit Media-Independent Interface (RGMII) Specification Version 1.3* (12/10/2000). The RMII interface follows the *RMII Consortium RMII Specification Version 1.2* (3/20/1998). The electrical characteristics for MDIO and MDC are specified in Section 9, "Ethernet Management Interface Electrical Characteristics."

8.1.1 eTSEC DC Electrical Characteristics

All GMII, MII, TBI, RGMII, RMII, and RTBI drivers and receivers comply with the DC parametric attributes specified in Table 22 and Table 23. The RGMII and RTBI signals are based on a 2.5-V CMOS interface voltage as defined by JEDEC EIA/JESD8-5.

Table 22. GMII, MII, RMII, and TBI DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit	Notes
Supply voltage 3.3 V	LV_{DD} TV_{DD}	3.13	3.47	V	1, 2
Output high voltage (LV_{DD}/TV_{DD} = min, I_{OH} = –4.0 mA)	V_{OH}	2.40	LV_{DD}/TV_{DD} + 0.3	V	—
Output low voltage (LV_{DD}/TV_{DD} = min, I_{OL} = 4.0 mA)	V_{OL}	GND	0.50	V	—
Input high voltage	V_{IH}	2.0	LV_{DD}/TV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	0.90	V	—
Input high current (V_{IN} = LV_{DD}, V_{IN} = TV_{DD})	I_{IH}	—	40	μA	1, 2, 3
Input low current (V_{IN} = GND)	I_{IL}	–600	—	μA	—

Notes:
1. LV_{DD} supports eTSECs 1 and 2.
2. TV_{DD} supports eTSECs 3 and 4.
3. The symbol V_{IN}, in this case, represents the LV_{IN} and TV_{IN} symbols referenced in Table 1 and Table 2.

Figure 10 shows the GMII receive AC timing diagram.

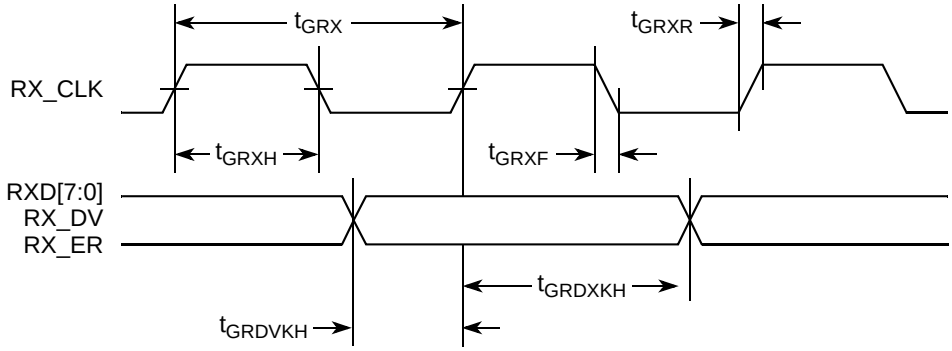

Figure 10. GMII Receive AC Timing Diagram

8.2.3 MII AC Timing Specifications

This section describes the MII transmit and receive AC timing specifications.

8.2.3.1 MII Transmit AC Timing Specifications

This table provides the MII transmit AC timing specifications.

Table 28. MII Transmit AC Timing Specifications

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
TX_CLK clock period 10 Mbps	t_{MTX}[2]	—	400	—	ns
TX_CLK clock period 100 Mbps	t_{MTX}	—	40	—	ns
TX_CLK duty cycle	t_{MTXH}/t_{MTX}	35	—	65	%
TX_CLK to MII data TXD[3:0], TX_ER, TX_EN delay	t_{MTKHDX}	1	5	15	ns
TX_CLK data clock rise (20%–80%)	t_{MTXR}[2]	1.0	—	4.0	ns
TX_CLK data clock fall (80%–20%)	t_{MTXF}[2]	1.0	—	4.0	ns

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MTKHDX} symbolizes MII transmit timing (MT) for the time t_{MTX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{MTX} represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. Guaranteed by design.

Figure 13 shows the MII receive AC timing diagram.

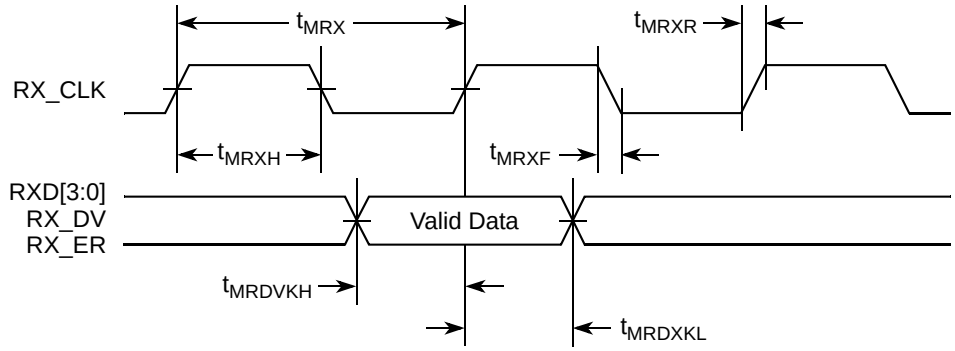

Figure 13. MII Receive AC Timing Diagram

8.2.4 TBI AC Timing Specifications

This section describes the TBI transmit and receive AC timing specifications.

8.2.4.1 TBI Transmit AC Timing Specifications

This table provides the TBI transmit AC timing specifications.

Table 30. TBI Transmit AC Timing Specifications

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
TCG[9:0] setup time GTX_CLK going high	t_{TTKHDV}	2.0	—	—	ns
TCG[9:0] hold time from GTX_CLK going high	t_{TTKHDX}	1.0	—	—	ns
GTX_CLK rise (20%–80%)	t_{TTXR}[2]	—	—	1.0	ns
GTX_CLK fall time (80%–20%)	t_{TTXF}[2]	—	—	1.0	ns

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{TTKHDV} symbolizes the TBI transmit timing (TT) with respect to the time from t_{TTX} (K) going high (H) until the referenced data signals (D) reach the valid state (V) or setup time. Also, t_{TTKHDX} symbolizes the TBI transmit timing (TT) with respect to the time from t_{TTX} (K) going high (H) until the referenced data signals (D) reach the invalid state (X) or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{TTX} represents the TBI (T) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. Guaranteed by design.

10 Local Bus

This section describes the DC and AC electrical specifications for the local bus interface of the device.

10.1 Local Bus DC Electrical Characteristics

This table provides the DC electrical characteristics for the local bus interface operating at BV_{DD} = 3.3 V DC.

Table 38. Local Bus DC Electrical Characteristics (3.3 V DC)

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	BV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current (V_{IN}[1] = 0 V or V_{IN} = BV_{DD})	I_{IN}	—	±5	μA
High-level output voltage (BV_{DD} = min, I_{OH} = –2 mA)	V_{OH}	2.4	—	V
Low-level output voltage (BV_{DD} = min, I_{OL} = 2 mA)	V_{OL}	—	0.4	V

Note:
1. Note that the symbol V_{IN}, in this case, represents the BV_{IN} symbol referenced in Table 1 and Table 2.

Table 39 provides the DC electrical characteristics for the local bus interface operating at BV_{DD} = 2.5 V DC.

Table 39. Local Bus DC Electrical Characteristics (2.5 V DC)

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	1.70	BV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.7	V
Input current (V_{IN}[1] = 0 V or V_{IN} = BV_{DD})	I_{IH}	—	10	μA
	I_{IL}		–15	
High-level output voltage (BV_{DD} = min, I_{OH} = –1 mA)	V_{OH}	2.0	—	V
Low-level output voltage (BV_{DD} = min, I_{OL} = 1 mA)	V_{OL}	—	0.4	V

Note:
1. Note that the symbol V_{IN}, in this case, represents the BV_{IN} symbol referenced in Table 1 and Table 2.

10.2 Local Bus AC Electrical Specifications

This table describes the timing parameters of the local bus interface at BV_{DD} = 3.3 V. For information about the frequency range of local bus, see Section 20.1, "Clock Ranges."

Table 40. Local Bus Timing Parameters (BV_{DD} = 3.3 V)—PLL Enabled

Parameter	Symbol[1]	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	7.5	12	ns	2
Local bus duty cycle	t_{LBKH}/t_{LBK}	43	57	%	—
LCLK[n] skew to LCLK[m] or LSYNC_OUT	$t_{LBKSKEW}$	—	150	ps	7, 8
Input setup to local bus clock (except $\overline{\text{LGTA}}$/LUPWAIT)	$t_{LBIVKH1}$	1.8	—	ns	3, 4
$\overline{\text{LGTA}}$/LUPWAIT input setup to local bus clock	$t_{LBIVKH2}$	1.7	—	ns	3, 4
Input hold from local bus clock (except $\overline{\text{LGTA}}$/LUPWAIT)	$t_{LBIXKH1}$	1.0	—	ns	3, 4
$\overline{\text{LGTA}}$/LUPWAIT input hold from local bus clock	$t_{LBIXKH2}$	1.0	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH hold time)	t_{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	$t_{LBKHOV1}$	—	2.0	ns	—
Local bus clock to data valid for LAD/LDP	$t_{LBKHOV2}$	—	2.2	ns	3
Local bus clock to address valid for LAD	$t_{LBKHOV3}$	—	2.3	ns	3
Local bus clock to LALE assertion	$t_{LBKHOV4}$	—	2.3	ns	3
Output hold from local bus clock (except LAD/LDP and LALE)	$t_{LBKHOX1}$	0.7	—	ns	3
Output hold from local bus clock for LAD/LDP	$t_{LBKHOX2}$	0.7	—	ns	3
Local bus clock to output high Impedance (except LAD/LDP and LALE)	$t_{LBKHOZ1}$	—	2.5	ns	5
Local bus clock to output high impedance for LAD/LDP	$t_{LBKHOZ2}$	—	2.5	ns	5

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to LSYNC_IN for PLL enabled and internal local bus clock for PLL bypass mode.
3. All signals are measured from $BV_{DD}/2$ of the rising edge of LSYNC_IN for PLL enabled or internal local bus clock for PLL bypass mode to $0.4 \times BV_{DD}$ of the signal in question for 3.3-V signaling levels.
4. Input timings are measured at the pin.
5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
6. t_{LBOTOT} is a measurement of the minimum time between the negation of LALE and any change in LAD. t_{LBOTOT} is programmed with the LBCR[AHD] parameter.
7. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[*n*]. Skew measured between complementary signals at $BV_{DD}/2$.
8. Guaranteed by design.

of a balanced interchange circuit and ground. In this example, for SerDes output, V_{cm_out} = V_{SD_TX} + $V_{\overline{SD\_TX}}$ = (A + B)/2, which is the arithmetic mean of the two complimentary output voltages within a differential pair. In a system, the common mode voltage may often differ from one component's output to the other's input. Sometimes, it may be even different between the receiver input and driver output circuits within the same component. It is also referred to as the DC offset.

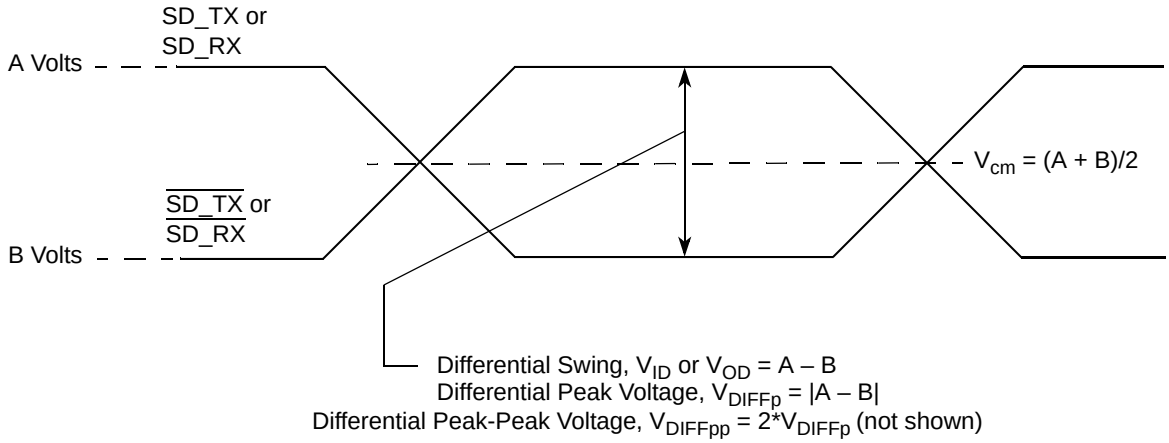

Figure 38. Differential Voltage Definitions for Transmitter or Receiver

To illustrate these definitions using real values, consider the case of a CML (current mode logic) transmitter that has a common mode voltage of 2.25 V and each of its outputs, TD and $\overline{TD}$, has a swing that goes between 2.5 and 2.0 V. Using these values, the peak-to-peak voltage swing of each signal (TD or $\overline{TD}$) is 500 mVp-p, which is referred as the single-ended swing for each signal. In this example, since the differential signaling environment is fully symmetrical, the transmitter output's differential swing (V_{OD}) has the same amplitude as each signal's single-ended swing. The differential output signal ranges between 500 and –500 mV, in other words, V_{OD} is 500 mV in one phase and –500 mV in the other phase. The peak differential voltage (V_{DIFFp}) is 500 mV. The peak-to-peak differential voltage ($V_{DIFFp-p}$) is 1000 mVp-p.

16.2 SerDes Reference Clocks

The SerDes reference clock inputs are applied to an internal PLL whose output creates the clock used by the corresponding SerDes lanes. The SerDes reference clocks inputs are SD_REF_CLK and $\overline{SD\_REF\_CLK}$ for PCI Express and serial RapidIO.

The following sections describe the SerDes reference clock requirements and some application information.

16.2.1 SerDes Reference Clock Receiver Characteristics

Figure 39 shows a receiver reference diagram of the SerDes reference clocks.

- The supply voltage requirements for XV_{DD_SRDS2} are specified in Table 1 and Table 2.
- SerDes Reference clock receiver reference circuit structure:

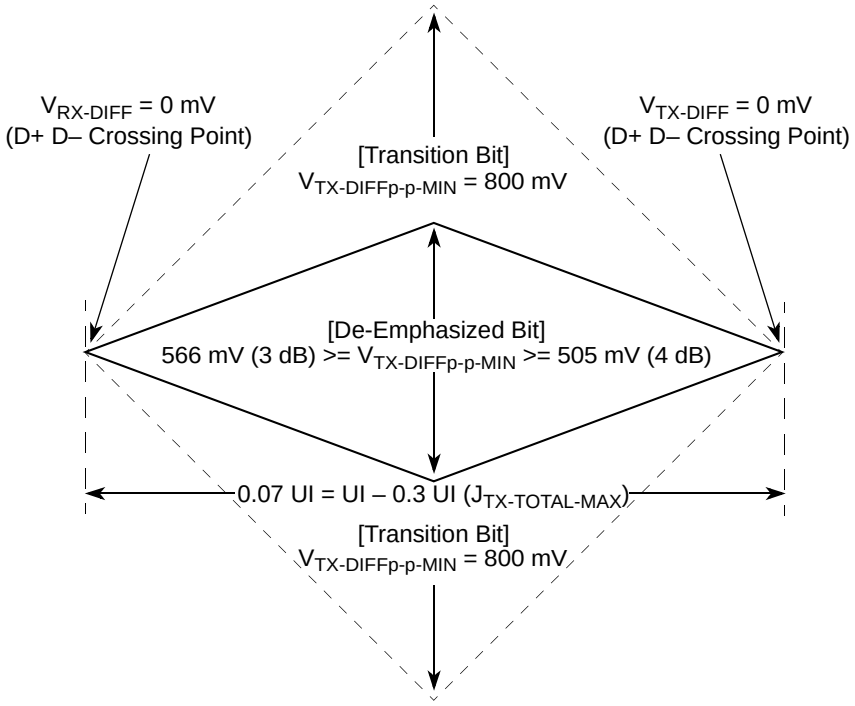

Figure 48. Minimum Transmitter Timing and Voltage Output Compliance Specifications

17.4.3 Differential Receiver (RX) Input Specifications

Table 57 defines the specifications for the differential input at all receivers (RXs). The parameters are specified at the component pins.

Table 57. Differential Receiver (RX) Input Specifications

Symbol	Parameter	Min	Nom	Max	Unit	Comments
UI	Unit interval	399.88	400	400.12	ps	Each UI is 400 ps ± 300 ppm. UI does not account for spread spectrum clock dictated variations. See Note 1.
$V_{RX-DIFFp-p}$	Differential peak-to-peak input voltage	0.175	—	1.200	V	$V_{RX-DIFFp-p} = 2 \times \lvert V_{RX-D+} - V_{RX-D-}\rvert$. See Note 2.
T_{RX-EYE}	Minimum receiver eye width	0.4	—	—	UI	The maximum interconnect media and transmitter jitter that can be tolerated by the receiver can be derived as $T_{RX-MAX-JITTER} = 1 - T_{RX-EYE} = 0.6$ UI. See Notes 2 and 3.
$T_{RX-EYE-MEDIAN-to-MAX-JITTER}$	Maximum time between the jitter median and maximum deviation from the median	—	—	0.3	UI	Jitter is defined as the measurement variation of the crossing points ($V_{RX-DIFFp-p}$ = 0 V) in relation to a recovered TX UI. A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. Jitter is measured using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI. See Notes 2, 3, and 7.

The eye diagram must be valid for any 250 consecutive UIs.

A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. The eye diagram is created using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI.

NOTE

The reference impedance for return loss measurements is 50. to ground for both the D+ and D– line (that is, as measured by a vector network analyzer with 50-Ω probes—see Figure 50). Note that the series capacitors, CTX, are optional for the return loss measurement.

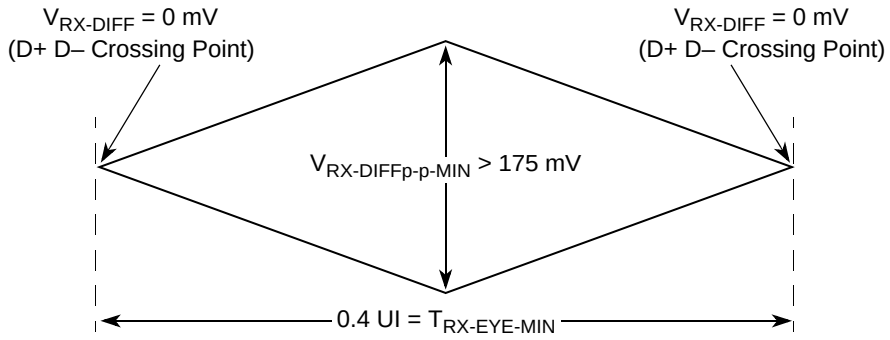

Figure 49. Minimum Receiver Eye Timing and Voltage Compliance Specification

17.5.1 Compliance Test and Measurement Load

The AC timing and voltage parameters must be verified at the measurement point, as specified within 0.2 inches of the package pins, into a test/measurement load shown in Figure 50.

NOTE

The allowance of the measurement point to be within 0.2 inches of the package pins is meant to acknowledge that package/board routing may benefit from D+ and D– not being exactly matched in length at the package pin boundary.

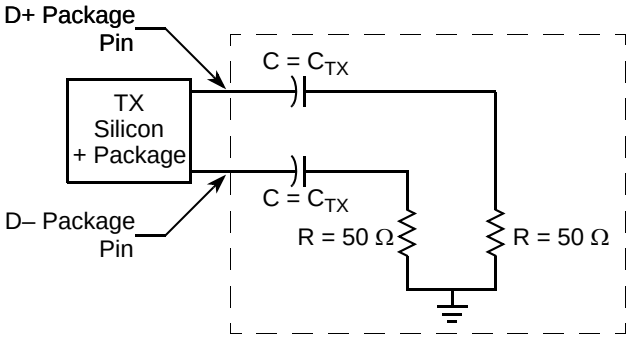

Figure 50. Compliance Test/Measurement Load

Table 71. MPC8548E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
LV_{DD}	N8, R7, T9, U6	Power for TSEC1 and TSEC2 (2.5 V, 3.3 V)	LV_{DD}	—
TV_{DD}	W9, Y6	Power for TSEC3 and TSEC4 (2,5 V, 3.3 V)	TV_{DD}	—
GV_{DD}	B3, B11, C7, C9, C14, C17, D4, D6, D10, D15, E2, E8, E11, E18, F5, F12, F16, G3, G7, G9, G11, H5, H12, H15, H17, J10, K3, K12, K16, K18, L6, M4, M8, M13	Power for DDR1 and DDR2 DRAM I/O voltage (1.8 V, 2.5)	GV_{DD}	—
BV_{DD}	C21, C24, C27, E20, E25, G19, G23, H26, J20	Power for local bus (1.8 V, 2.5 V, 3.3 V)	BV_{DD}	—
V_{DD}	M19, N12, N14, N16, N18, P11, P13, P15, P17, P19, R12, R14, R16, R18, T11, T13, T15, T17, T19, U12, U14, U16, U18, V17, V19	Power for core (1.1 V)	V_{DD}	—
SV_{DD}	L25, L27, M24, N28, P24, P26, R24, R27, T25, V24, V26, W24, W27, Y25, AA28, AC27	Core Power for SerDes transceivers (1.1 V)	SV_{DD}	—
XV_{DD}	L20, L22, N23, P21, R22, T20, U23, V21, W22, Y20	Pad Power for SerDes transceivers (1.1 V)	XV_{DD}	—
AVDD_LBIU	J28	Power for local bus PLL (1.1 V)	—	26
AVDD_PCI1	AH21	Power for PCI1 PLL (1.1 V)	—	26
AVDD_PCI2	AH22	Power for PCI2 PLL (1.1 V)	—	26
AVDD_CORE	AH15	Power for e500 PLL (1.1 V)	—	26
AVDD_PLAT	AH19	Power for CCB PLL (1.1 V)	—	26
AVDD_SRDS	U25	Power for SRDSPLL (1.1 V)	—	26
SENSEVDD	M14	O	V_{DD}	13

Table 71. MPC8548E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
SENSEVSS	M16	—	—	13
Analog Signals				
MVREF	A18	I Reference voltage signal for DDR	MVREF	—
SD_IMP_CAL_RX	L28	I	200Ω to GND	—
SD_IMP_CAL_TX	AB26	I	100Ω to GND	—
SD_PLL_TPA	U26	O	—	24

Notes:

1. All multiplexed signals are listed only once and do not re-occur. For example, $\overline{\text{LCS5}}$/$\overline{\text{DMA\_REQ2}}$ is listed only once in the local bus controller section, and is not mentioned in the DMA section even though the pin also functions as $\overline{\text{DMA\_REQ2}}$.
2. Recommend a weak pull-up resistor (2–10 kΩ) be placed on this pin to OV_{DD}.
3. A valid clock must be provided at POR if TSEC4_TXD[2] is set = 1.
4. This pin is an open drain signal.
5. This pin is a reset configuration pin. It has a weak internal pull-up P-FET which is enabled only when the processor is in the reset state. This pull-up is designed such that it can be overpowered by an external 4.7-kΩ pull-down resistor. However, if the signal is intended to be high after reset, and if there is any device on the net which might pull down the value of the net at reset, then a pullup or active driver is needed.
6. Treat these pins as no connects (NC) unless using debug address functionality.
7. The value of LA[28:31] during reset sets the CCB clock to SYSCLK PLL ratio. These pins require 4.7-kΩ pull-up or pull-down resistors. See Section 20.2, “CCB/SYSCLK PLL Ratio.”
8. The value of LALE, LGPL2, and LBCTL at reset set the e500 core clock to CCB clock PLL ratio. These pins require 4.7-kΩ pull-up or pull-down resistors. See the Section 20.3, “e500 Core PLL Ratio.”
9. Functionally, this pin is an output, but structurally it is an I/O because it either samples configuration input during reset or because it has other manufacturing test functions. This pin therefore is described as an I/O for boundary scan.
10. This pin functionally requires a pull-up resistor, but during reset it is a configuration input that controls 32- vs. 64-bit PCI operation. Therefore, it must be actively driven low during reset by reset logic if the device is to be configured to be a 64-bit PCI device. See the *PCI Specification*.
11. This output is actively driven during reset rather than being three-stated during reset.
12. These JTAG pins have weak internal pull-up P-FETs that are always enabled.
13. These pins are connected to the V_{DD}/GND planes internally and may be used by the core power supply to improve tracking and regulation.
14. Internal thermally sensitive resistor.
15. No connections must be made to these pins if they are not used.
16. These pins are not connected for any use.
17. PCI specifications recommend that a weak pull-up resistor (2–10 kΩ) be placed on the higher order pins to OV_{DD} when using 64-bit buffer mode (pins PCI_AD[63:32] and $\overline{\text{PCI1\_C\_BE}}$[7:4]).
19. If this pin is connected to a device that pulls down during reset, an external pull-up is required to drive this pin to a safe state during reset.
20. This pin is only an output in FIFO mode when used as Rx flow control.
24. Do not connect.

Table 71. MPC8548E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes

25.These are test signals for factory use only and must be pulled up (100 Ω–1 kΩ) to OV_{DD} for normal machine operation.

26.Independent supplies derived from board V_{DD}.

27.Recommend a pull-up resistor (~1 kΩ) be placed on this pin to OV_{DD}.

29. The following pins must NOT be pulled down during power-on reset: TSEC3_TXD[3], TSEC4_TXD3/TSEC3_TXD7, HRESET_REQ, TRIG_OUT/READY/QUIESCE, MSRCID[2:4], ASLEEP.

30.This pin requires an external 4.7-kΩ pull-down resistor to prevent PHY from seeing a valid transmit enable before it is actively driven.

31.This pin is only an output in eTSEC3 FIFO mode when used as Rx flow control.

32.These pins must be connected to XV_{DD}.

33.TSEC2_TXD1, TSEC2_TX_ER are multiplexed as cfg_dram_type[0:1]. They must be valid at power-up, even before HRESET assertion.

34.These pins must be pulled to ground through a 300-Ω (±10%) resistor.

35.When a PCI block is disabled, either the POR config pin that selects between internal and external arbiter must be pulled down to select external arbiter if there is any other PCI device connected on the PCI bus, or leave the PCI*n*_AD pins as 'no connect' or terminated through 2–10 kΩ pull-up resistors with the default of internal arbiter if the PCI*n*_AD pins are not connected to any other PCI device. The PCI block drives the PCI*n*_AD pins if it is configured to be the PCI arbiter—through POR config pins—irrespective of whether it is disabled via the DEVDISR register or not. It may cause contention if there is any other PCI device connected on the bus.

36.MDIC0 is grounded through an 18.2-Ω precision 1% resistor and MDIC1 is connected to GV_{DD} through an 18.2-Ω precision 1% resistor. These pins are used for automatic calibration of the DDR IOs.

38.These pins must be left floating.

39. If PCI1 or PCI2 is configured as PCI asynchronous mode, a valid clock must be provided on pin PCI1_CLK or PCI2_CLK. Otherwise the processor will not boot up.

40.These pins must be connected to GND.

101.This pin requires an external 4.7-kΩ resistor to GND.

102.For Rev. 2.x silicon, DMA_DACK[0:1] must be 0b11 during POR configuration; for rev. 1.x silicon, the pin values during POR configuration are don't care.

103.If these pins are not used as GPIN*n* (general-purpose input), they must be pulled low (to GND) or high (to LV_{DD}) through 2–10 kΩ resistors.

104.These must be pulled low to GND through 2–10 kΩ resistors if they are not used.

105.These must be pulled low or high to LV_{DD} through 2–10 kΩ resistors if they are not used.

106.For rev. 2.x silicon, DMA_DACK[0:1] must be 0b10 during POR configuration; for rev. 1.x silicon, the pin values during POR configuration are don't care.

107.For rev. 2.x silicon, DMA_DACK[0:1] must be 0b01 during POR configuration; for rev. 1.x silicon, the pin values during POR configuration are don't care.

108.For rev. 2.x silicon, DMA_DACK[0:1] must be 0b11 during POR configuration; for rev. 1.x silicon, the pin values during POR configuration are don't care.

109.This is a test signal for factory use only and must be pulled down (100 Ω – 1 kΩ) to GND for normal machine operation.

110.These pins must be pulled high to OV_{DD} through 2–10 kΩ resistors.

111.If these pins are not used as GPIN*n* (general-purpose input), they must be pulled low (to GND) or high (to OV_{DD}) through 2–10 kΩ resistors.

112.This pin must not be pulled down during POR configuration.

113.These should be pulled low or high to OV_{DD} through 2–10 kΩ resistors.

Table 72. MPC8547E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
Reserved	U20, V22, W20, Y22	—	—	15
Reserved	U21, V23, W21, Y23	—	—	15
SD_PLL_TPD	U28	O	XV_{DD}	24
SD_REF_CLK	T28	I	XV_{DD}	—
$\overline{\text{SD\_REF\_CLK}}$	T27	I	XV_{DD}	—
Reserved	AC1, AC3	—	—	2
Reserved	M26, V28	—	—	32
Reserved	M25, V27	—	—	34
Reserved	M20, M21, T22, T23	—	—	38
General-Purpose Output				
GPOUT[24:31]	K26, K25, H27, G28, H25, J26, K24, K23	O	BV_{DD}	—
System Control				
$\overline{\text{HRESET}}$	AG17	I	OV_{DD}	—
$\overline{\text{HRESET\_REQ}}$	AG16	O	OV_{DD}	29
$\overline{\text{SRESET}}$	AG20	I	OV_{DD}	—
$\overline{\text{CKSTP\_IN}}$	AA9	I	OV_{DD}	—
$\overline{\text{CKSTP\_OUT}}$	AA8	O	OV_{DD}	2, 4
Debug				
TRIG_IN	AB2	I	OV_{DD}	—
TRIG_OUT/READY/$\overline{\text{QUIESCE}}$	AB1	O	OV_{DD}	6, 9, 19, 29
MSRCID[0:1]	AE4, AG2	O	OV_{DD}	5, 6, 9
MSRCID[2:4]	AF3, AF1, AF2	O	OV_{DD}	6, 19, 29
MDVAL	AE5	O	OV_{DD}	6
CLK_OUT	AE21	O	OV_{DD}	11
Clock				
RTC	AF16	I	OV_{DD}	—
SYSCLK	AH17	I	OV_{DD}	—
JTAG				
TCK	AG28	I	OV_{DD}	—
TDI	AH28	I	OV_{DD}	12
TDO	AF28	O	OV_{DD}	—
TMS	AH27	I	OV_{DD}	12
$\overline{\text{TRST}}$	AH23	I	OV_{DD}	12

Table 74. MPC8543E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
$\overline{\text{MWE}}$	E7	O	GV_{DD}	—
$\overline{\text{MCAS}}$	H7	O	GV_{DD}	—
$\overline{\text{MRAS}}$	L8	O	GV_{DD}	—
MCKE[0:3]	F10, C10, J11, H11	O	GV_{DD}	11
$\overline{\text{MCS}}$[0:3]	K8, J8, G8, F8	O	GV_{DD}	—
MCK[0:5]	H9, B15, G2, M9, A14, F1	O	GV_{DD}	—
$\overline{\text{MCK}}$[0:5]	J9, A15, G1, L9, B14, F2	O	GV_{DD}	—
MODT[0:3]	E6, K6, L7, M7	O	GV_{DD}	—
MDIC[0:1]	A19, B19	I/O	GV_{DD}	36
Local Bus Controller Interface				
LAD[0:31]	E27, B20, H19, F25, A20, C19, E28, J23, A25, K22, B28, D27, D19, J22, K20, D28, D25, B25, E22, F22, F21, C25, C22, B23, F20, A23, A22, E19, A21, D21, F19, B21	I/O	BV_{DD}	—
LDP[0:3]	K21, C28, B26, B22	I/O	BV_{DD}	—
LA[27]	H21	O	BV_{DD}	5, 9
LA[28:31]	H20, A27, D26, A28	O	BV_{DD}	5, 7, 9
$\overline{\text{LCS}}$[0:4]	J25, C20, J24, G26, A26	O	BV_{DD}	—
$\overline{\text{LCS5}}$/$\overline{\text{DMA\_DREQ2}}$	D23	I/O	BV_{DD}	1
$\overline{\text{LCS6}}$/$\overline{\text{DMA\_DACK2}}$	G20	O	BV_{DD}	1
$\overline{\text{LCS7}}$/$\overline{\text{DMA\_DDONE2}}$	E21	O	BV_{DD}	1
$\overline{\text{LWE0}}$/$\overline{\text{LBS0}}$/LSDDQM[0]	G25	O	BV_{DD}	5, 9
$\overline{\text{LWE1}}$/$\overline{\text{LBS1}}$/LSDDQM[1]	C23	O	BV_{DD}	5, 9
$\overline{\text{LWE2}}$/$\overline{\text{LBS2}}$/LSDDQM[2]	J21	O	BV_{DD}	5, 9
$\overline{\text{LWE3}}$/$\overline{\text{LBS3}}$/LSDDQM[3]	A24	O	BV_{DD}	5, 9
LALE	H24	O	BV_{DD}	5, 8, 9
LBCTL	G27	O	BV_{DD}	5, 8, 9
LGPL0/LSDA10	F23	O	BV_{DD}	5, 9
LGPL1/$\overline{\text{LSDWE}}$	G22	O	BV_{DD}	5, 9
LGPL2/$\overline{\text{LOE}}$/$\overline{\text{LSDRAS}}$	B27	O	BV_{DD}	5, 8, 9
LGPL3/$\overline{\text{LSDCAS}}$	F24	O	BV_{DD}	5, 9
LGPL4/$\overline{\text{LGTA}}$/LUPWAIT/LPBSE	H23	I/O	BV_{DD}	—
LGPL5	E26	O	BV_{DD}	5, 9
LCKE	E24	O	BV_{DD}	—
LCLK[0:2]	E23, D24, H22	O	BV_{DD}	—

Table 74. MPC8543E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
TV_{DD}	W9, Y6	Power for TSEC3 and TSEC4 (2,5 V, 3.3 V)	TV_{DD}	—
GV_{DD}	B3, B11, C7, C9, C14, C17, D4, D6, D10, D15, E2, E8, E11, E18, F5, F12, F16, G3, G7, G9, G11, H5, H12, H15, H17, J10, K3, K12, K16, K18, L6, M4, M8, M13	Power for DDR1 and DDR2 DRAM I/O voltage (1.8 V,2.5 V)	GV_{DD}	—
BV_{DD}	C21, C24, C27, E20, E25, G19, G23, H26, J20	Power for local bus (1.8 V, 2.5 V, 3.3 V)	BV_{DD}	—
V_{DD}	M19, N12, N14, N16, N18, P11, P13, P15, P17, P19, R12, R14, R16, R18, T11, T13, T15, T17, T19, U12, U14, U16, U18, V17, V19	Power for core (1.1 V)	V_{DD}	—
SV_{DD}	L25, L27, M24, N28, P24, P26, R24, R27, T25, V24, V26, W24, W27, Y25, AA28, AC27	Core power for SerDes transceivers (1.1 V)	SV_{DD}	—
XV_{DD}	L20, L22, N23, P21, R22, T20, U23, V21, W22, Y20	Pad power for SerDes transceivers (1.1 V)	XV_{DD}	—
AVDD_LBIU	J28	Power for local bus PLL (1.1 V)	—	26
AVDD_PCI1	AH21	Power for PCI1 PLL (1.1 V)	—	26
AVDD_PCI2	AH22	Power for PCI2 PLL (1.1 V)	—	26
AVDD_CORE	AH15	Power for e500 PLL (1.1 V)	—	26
AVDD_PLAT	AH19	Power for CCB PLL (1.1 V)	—	26
AVDD_SRDS	U25	Power for SRDSPLL (1.1 V)	—	26
SENSEVDD	M14	O	V_{DD}	13

as shown in Figure 63. If this is not possible, the isolation resistor allows future access to $\overline{\text{TRST}}$ in case a JTAG interface may need to be wired onto the system in future debug situations.

- No pull-up/pull-down is required for TDI, TMS, TDO, or TCK.

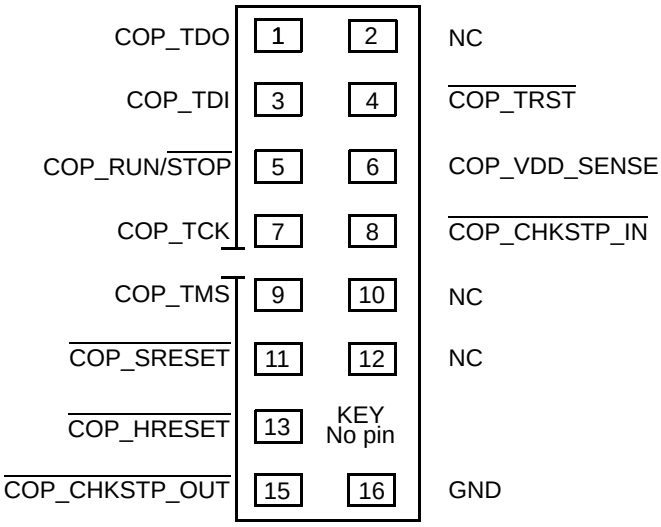

Figure 62. COP Connector Physical Pinout